

/ Descriptions

WR0<50 P ММ Ё QSQ Æ М ы s ll 1 Silicon NPN transistor in a TO-92LM Plastic Package.

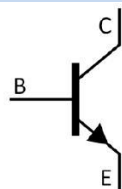
/ Features

Љ 5VD<98 Ы ´
Complementary to 2SA965.

/ Applications

Љ Æ Æ - Љ Æ Æ / Æ Љ Æ Æ
Audio frequency amplifier and driver stage amplifier Applications.

/ Equivalent Circuit



/ Pinning



PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

/ h_{FE} Classifications & Marking

h _{FE} Classifications Symbol	O	Y
h _{FE} Range	80 160	120 240

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	120	V
Collector to Emitter Voltage	V_{CEO}	120	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current (DC)	I_C	800	mA
Emitter Current	I_E	-800	mA
Collector Power Dissipation	P_C	900	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=10mA$ $I_B=0$	120			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=1.0mA$ $I_C=0$	5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=120V$ $I_E=0$			0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			0.1	μA

DC Current Gain β_{DC}

2SC2235

Rev.f.300./Mar.-2016



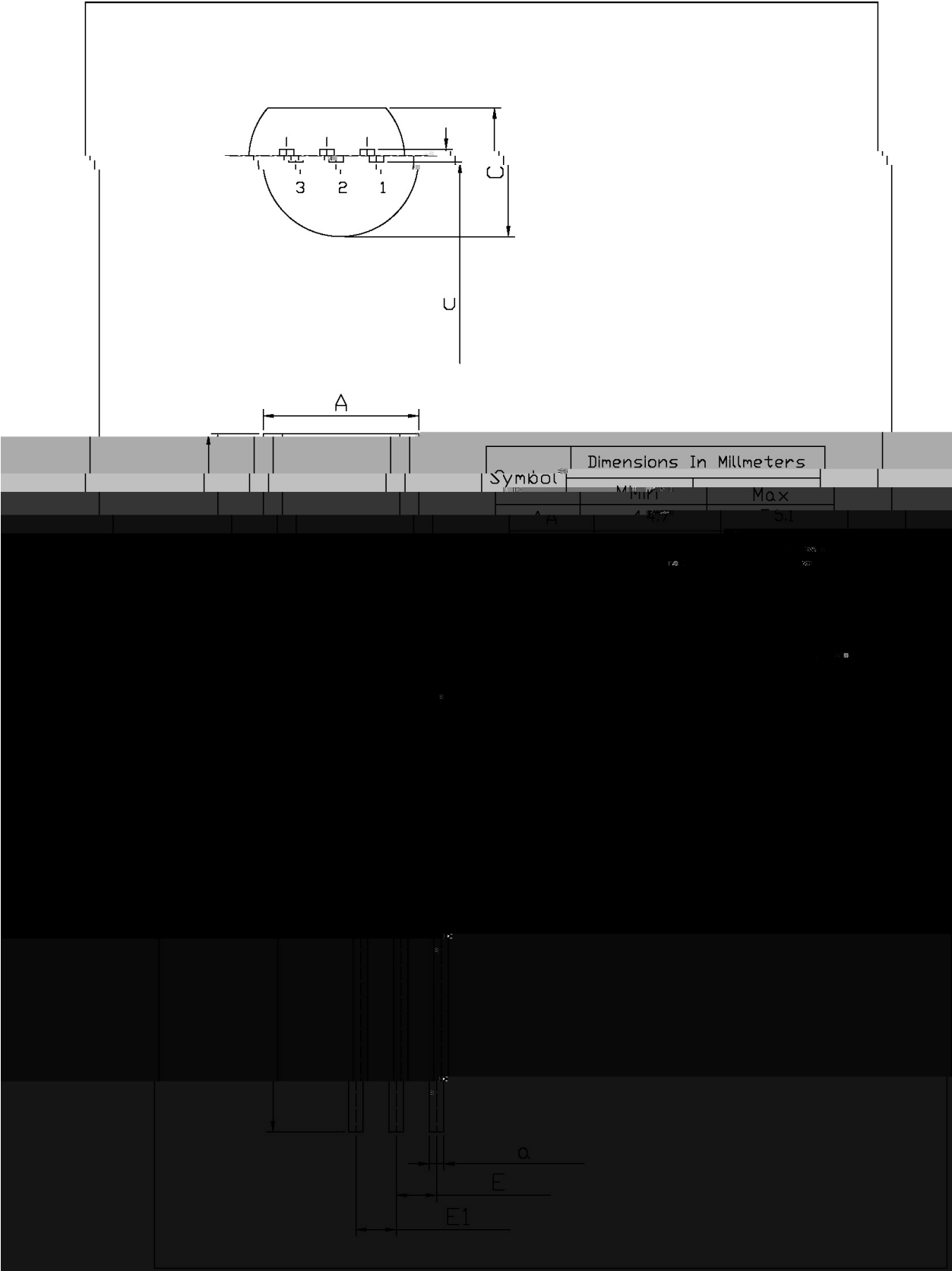
蓝箭电子
BLUE ROCKET ELECTRONICS

DATA SHEET

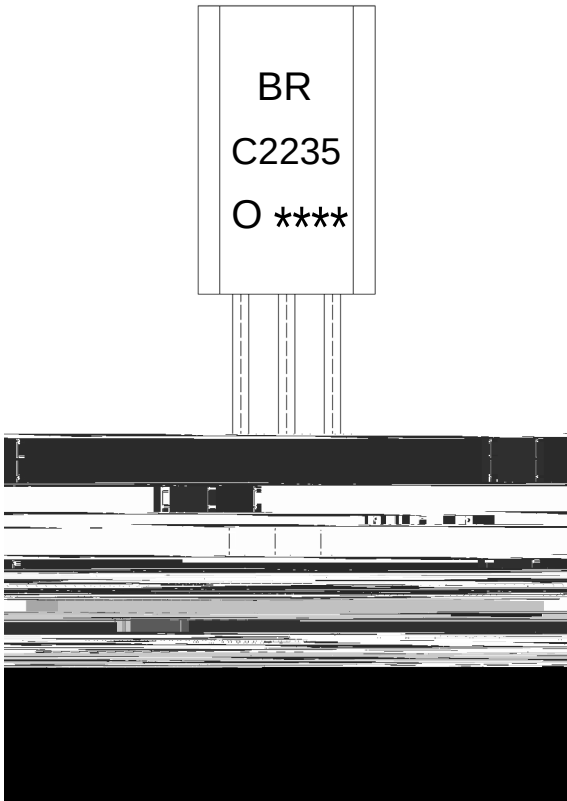
/ Package Dimensions

TO-92LM

Unit: mm

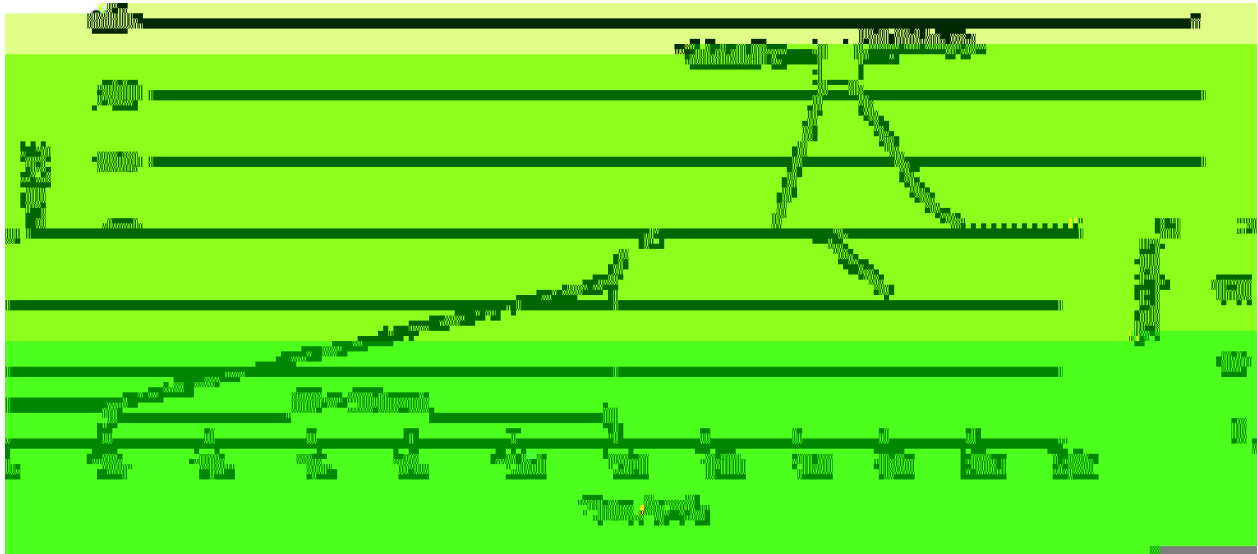


/ Marking Instructions



公司代码	公司代码
EU:	公司代码
F5568	公司代码
R:	公司代码
----	公司代码
Note:	
BR:	Company Code.
C2235:	Product Type.
O:	h _{FE} Classifications Symbol
****:	Lot No. Code,code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



б " X

1. 1. Preheating: 25~150 °C, Time: 60~90sec;
2. 2. Peak Temp.: 255 °C, Duration: 5 ° 0.5sec;
3. 3. Cooling Speed: 2~10 °C/sec.

Note:

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2. Peak Temp.: 255 °C, Duration: 5 ° 0.5sec.
3. Cooling Speed: 2~10 °C/sec.

/ Resistance to Soldering Heat Test Conditions

□ °C 270 ± 5 °C °C 10 ± 1 sec. Temp.: 270 ± 5 Time: 10 ± 1 sec

/ Packaging SPEC.

“Q” T Y E / BULK